


**REMARKS**

The Official Action mailed May 6, 2002 and the Advisory Action mailed September 9, 2002 have been received and their contents carefully noted. Filed concurrently herewith is a *Continued Prosecution Application (CPA) Request and Request for Three Month Extension of Time*, which extends the shortened statutory period for response to November 6, 2002. Accordingly, Applicant respectfully submits that this response is being timely filed.

Claims 1-12, 14-15, 18 and 20-29 are pending in the present application, of which claims 1-4, 14-15 and 28-29 are independent. All independent claims 1-4, 14-15 and 28-29 have been amended herewith and are believed to be in condition for allowance. By these amendments, all claims now recite an active matrix display device. Furthermore, claims 1, 2, 4, 15, and 28-29 have been amended to recite a patterning step to form a pixel electrode. These features of the presently pending claims are not believed to be disclosed or suggested by the prior art of record and are believed to patentably distinguish the claims over the outstanding rejections. Favorable consideration is requested.

Should the Examiner believe that anything further would be desirable to place this application in better condition for allowance, the Examiner is invited to contact Applicant's undersigned attorney at the telephone number listed below.

Respectfully submitted,

  
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**VERSION WITH MARKINGS TO SHOW CHANGES MADE**

**IN THE CLAIMS:**

Please amend claims 1-4, 14-15 and 28-29 as follows:

1. (Amended) A method for producing a semiconductor device having an active matrix display device, comprising:

forming a first conductive layer;

forming an insulating layer comprising an organic resin over said first conductive layer;

forming an opening in said insulating layer to expose said first conductive layer at a bottom of said opening;

forming an embedded conductive layer comprising an organic resin to cover said insulating layer and said opening;

etching or polishing said embedded conductive layer to expose a portion of the insulating layer; and

forming a second conductive layer on said insulating layer and said embedded conductive layer; and

forming a pixel electrode by patterning the second conductive layer, wherein said second conductive layer is light reflective.

2. (Amended) A method for producing a semiconductor device having an active matrix display device, comprising:

forming a first conductive layer;

forming an insulating layer over said first conductive layer;

forming an opening in said insulating layer to expose said first conductive layer at a bottom of said opening;

forming an oxide conductive layer by a spin coating method to cover said insulating layer and said opening;

etching or polishing said oxide conductive layer to make a state in that only said opening is filled with said oxide conductive layer; and

forming a second conductive layer on said insulating layer and said oxide conductive layer; and

forming a pixel electrode by patterning the second conductive layer, wherein said second conductive layer is light reflective.

3. (Amended) A method for producing a semiconductor device having an active matrix display device, comprising: forming an active layer of a transistor;

forming an insulating layer over said active layer;

forming an opening in said insulating layer to expose a portion of the active layer at a bottom of said opening;

forming an embedded conductive layer comprising a black colored material to cover said insulating layer and said opening wherein the embedded conductive layer contacts the active layer in the opening;

forming a transparent conductive layer on said embedded conductive layer;

patterning said transparent conductive layer to form a transparent pixel electrode.

4. (Amended) A method for producing a semiconductor device having an active matrix display device, comprising:

forming a first conductive layer;

forming an insulating layer over said first conductive layer;

forming an opening in said insulating layer to expose said first conductive layer at a bottom of said opening;

forming an oxide conductive layer by a spin coating method, to cover said insulating layer and said opening;

forming a second conductive layer on said oxide conductive layer;

patterning said second conductive layer to [a desired pattern] form a pixel electrode wherein said second conductive layer is light reflective, and

etching said oxide conductive layer by using said second conductive layer as a mask in a self alignment manner.

14. (Amended) A method for producing a semiconductor device having an active matrix display device, comprising:

- forming a first conductive layer;
  - forming an insulating layer over said first conductive layer;
  - forming an opening in said insulating layer to expose said first conductive layer at a bottom of said opening;
  - forming a second conductive layer comprising a conductive oxide to cover said insulating layer and said opening;
  - polishing said second conductive layer by employing a chemical mechanical polishing; and
  - forming a third conductive layer on said insulating layer and said second conductive layer,
- wherein said third conductive layer is reflective.

15. (Amended) A method for producing a semiconductor device having an active matrix display device, comprising:

- forming an active layer of a transistor;
- forming an insulating layer over the active layer;
- forming an opening in said insulating layer to expose a portion of the active layer at a bottom of said opening;
- forming a black colored conductive layer to cover said insulating layer and said opening;
- polishing said black colored conductive layer by employing a chemical mechanical polishing; and
- forming a second conductive layer on said insulating layer and said oxide conductive layer, wherein said second conductive layer is transparent; and
- forming a pixel electrode by patterning said second conductive layer.

28. (Amended) A method for producing a semiconductor device having an active matrix display device, comprising:

forming a first conductive layer;  
forming an insulating layer comprising an organic resin over said first conductive layer;  
forming an opening in said insulating layer to expose said first conductive layer at a bottom of said opening;  
forming an embedded conductive layer comprising an organic resin to cover said insulating layer and said opening;  
removing a portion of said embedded conductive layer to expose a portion of the insulating layer; and  
forming a second conductive layer on said insulating layer and said embedded conductive layer; and  
forming a pixel electrode by patterning the second conductive layer.

29. (Amended) A method for producing a semiconductor device having an active matrix display device, comprising:

forming a first conductive layer;  
forming an insulating layer over said first conductive layer;  
forming an opening in said insulating layer to expose said first conductive layer at a bottom of said opening;  
filling said opening with a second conductive layer comprising a conductive oxide to cover said insulating layer and said opening;  
forming a reflective pixel electrode on the insulating layer, wherein said reflective pixel electrode is electrically connected to the first conductive layer through the second conductive layer.